Product data sheet

1. General description

Planar passivated guaranteed commutation triac in a SOT223 surface mountable plastic package for use in motor control circuits or with other highly inductive loads. This triac balances the requirements of commutation performance and gate sensitivity and is intended for interfacing with low power drivers, including micro controllers.

2. Features and benefits

- · 3Q technology for improved noise immunity
- Direct triggering from low power drivers and logic ICs
- · High commutation capability with sensitive gate
- High immunity to false turn-on by dV/dt with sensitive gate
- Planar passivated for voltage ruggedness and reliability
- · Sensitive gate for easy logic level triggering
- Surface mountable package

3. Applications

- · General purpose motor controls
- Small loads in washing machines
- · Rectifier-fed DC inductive loads e.g. DC motors and solenoids

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DRM}	repetitive peak off- state voltage		-	-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 108 ^{\circ}\text{C}$; Fig. 2; Fig. 3	-	-	1	A
I _{TSM}	non-repetitive peak on- state current	full sine wave; $T_{j(init)}$ = 25 °C; t_p = 16.7 ms	-	-	11	А
		full sine wave; $T_{j(init)}$ = 25 °C; t_p = 20 ms; Fig. 4; Fig. 5	-	-	10	A
Tj	junction temperature		-	-	125	°C
Static charac	teristics					
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$ $T_j = 25 \text{ °C; } Fig. 9$	-	-	5	mA

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 9}}{}$	-	-	5	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	6	mA
V _T	on-state voltage	I _T = 2 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.2	1.5	V
Dynamic ch	aracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 0.1 V/µs; gate open circuit	5	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/ μ s; (snubberless condition); gate open circuit	1	-	-	A/ms

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	4	T2
2	T2	main terminal 2		G sym051
3	G	gate		Symosi
4	mb	mounting base; connected to T2	⊟1 ⊟2 ⊟3 SC-73 (SOT223)	

6. Ordering information

Table 3. Ordering information

Table of Ordering morniagen							
Type number	Package						
	Name	Description	Version				
BTA204W-600D	SC-73	plastic surface-mounted package with increased heatsink; 4 leads	SOT223				

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DRM}	repetitive peak off-state voltage		-	600	V
I _{T(RMS)}	RMS on-state current	full sine wave; $T_{sp} \le 108 \text{ °C}$; $Fig. 1$; $Fig. 2$; $Fig. 3$	-	1	Α
I _{TSM}	non-repetitive peak on-	full sine wave; $T_{j(init)} = 25 ^{\circ}C$; $t_p = 16.7 \text{ms}$	-	11	Α
	state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$; $t_p = 20 \text{ ms}$; Fig. 4; Fig. 5	-	10	A
I ² t	I ² t for fusing	t _p = 10 ms; SIN	-	0.5	A²s
dl _T /dt	rate of rise of on-state current	I _G = 0.2 A	-	100	A/µs
I _{GM}	peak gate current		-	1	Α
P_{GM}	peak gate power		-	5	W
P _{G(AV)}	average gate power	over any 20ms period	-	0.5	W
T _{stg}	storage temperature		-40	150	°C
T _j	junction temperature		-	125	°C

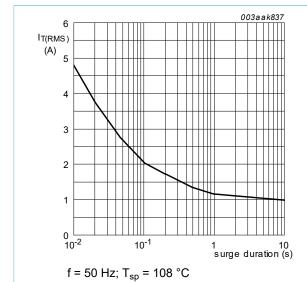


Fig. 1. RMS on-state current as a function of surge duration; maximum values

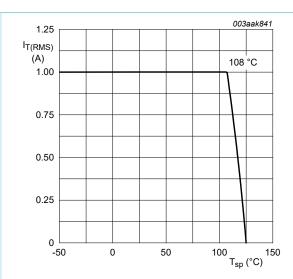


Fig. 2. RMS on-state current as a function of solder point temperature; maximum values

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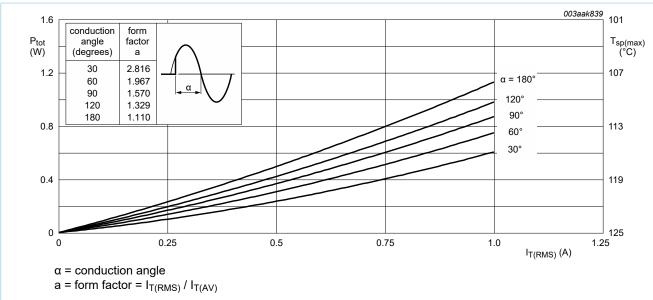


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

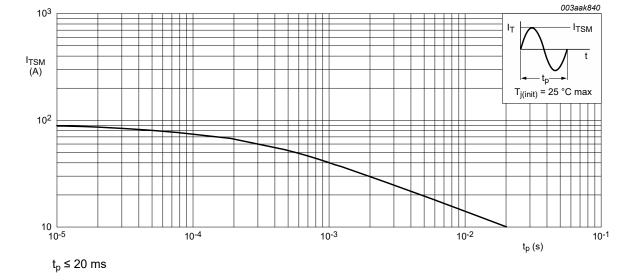


Fig. 4. Non-repetitive peak on-state current as a function of pulse width; maximum values

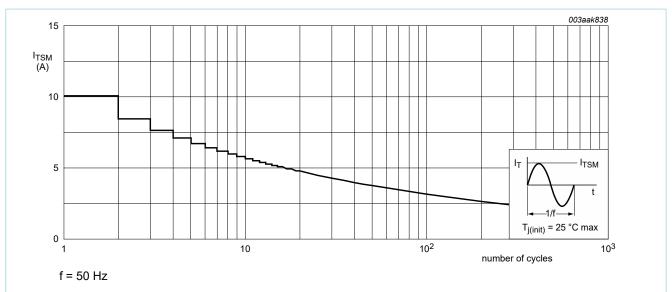


Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-sp)}	thermal resistance from junction to solder point	full cycle or half cycle; Fig. 6	-	-	15	K/W
$R_{th(j-a)}$	thermal resistance from junction to	printed circuit board mounted: minimum pad area; Fig. 7	-	70	-	K/W
	ambient free air	printed circuit board mounted: minimum footprint; Fig. 8	-	156	-	K/W

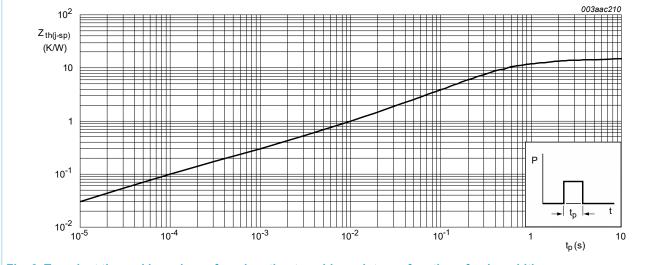
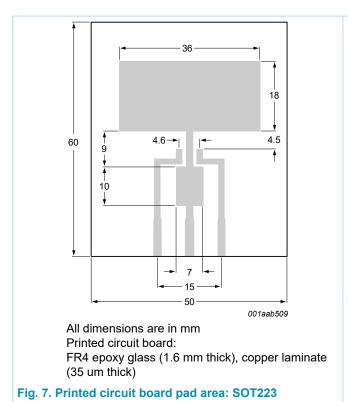


Fig. 6. Transient thermal impedance from junction to solder point as a function of pulse width



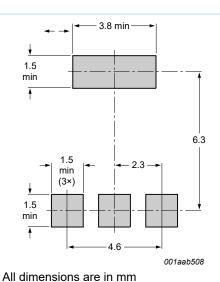


Fig. 8. Minimum footprint SOT223

9. Characteristics

Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics					,
I _{GT}	gate trigger current	V _D = 12 V; I _T = 0.1 A; T2+ G+; T _j = 25 °C; <u>Fig. 9</u>	-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	5	mA
		V _D = 12 V; I _T = 0.1 A; T2- G-; T _j = 25 °C; <u>Fig. 9</u>	-	-	5	mA
lL	latching current	V _D = 12 V; I _G = 0.1 A; T2+ G-; T _j = 25 °C; <u>Fig. 10</u>	-	-	6	mA
		$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. } 10}{\text{ C}}$	-	-	9	mA
		$V_D = 12 \text{ V; } I_G = 0.1 \text{ A; T2- G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. } 10}{\text{C}}$	-	-	6	mA
I _H	holding current	V _D = 12 V; T _j = 25 °C; <u>Fig. 11</u>	-	-	6	mA
V _T	on-state voltage	I _T = 2 A; T _j = 25 °C; <u>Fig. 12</u>	-	1.2	1.5	V
V _{GT}	gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 13	-	0.7	1	V
		V _D = 400 V; I _T = 0.1 A; T _j = 125 °C; Fig. 13	0.25	0.4	-	V
I _D	off-state current	V _D = 600 V; T _j = 125 °C	-	0.1	0.5	mA
Dynamic cl	haracteristics					
dV _D /dt	rate of rise of off-state voltage	V_{DM} = 402 V; T_j = 125 °C; (67% of V_{DRM}); exponential waveform; gate open circuit	20	-	-	V/µs
dl _{com} /dt	rate of change of commutating current	V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 0.1 V/ μ s; gate open circuit	5	-	-	A/ms
		V_D = 400 V; T_j = 125 °C; $I_{T(RMS)}$ = 1 A; dV_{com}/dt = 20 V/µs; (snubberless condition); gate open circuit	1	-	-	A/ms

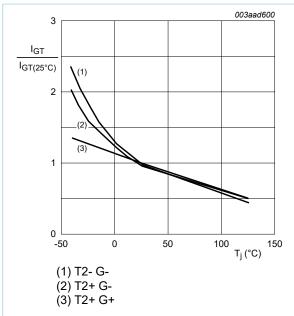


Fig. 9. Normalized gate trigger current as a function of junction temperature

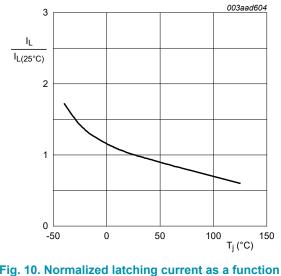


Fig. 10. Normalized latching current as a function of junction temperature

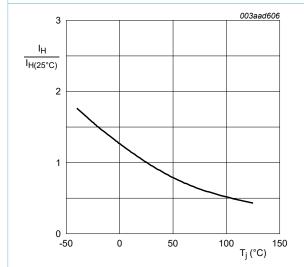
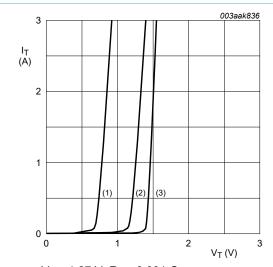


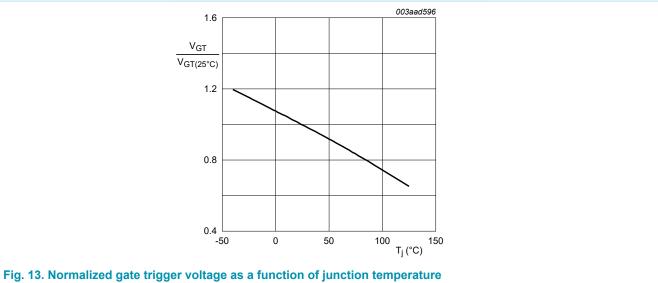
Fig. 11. Normalized holding current as a function of junction temperature



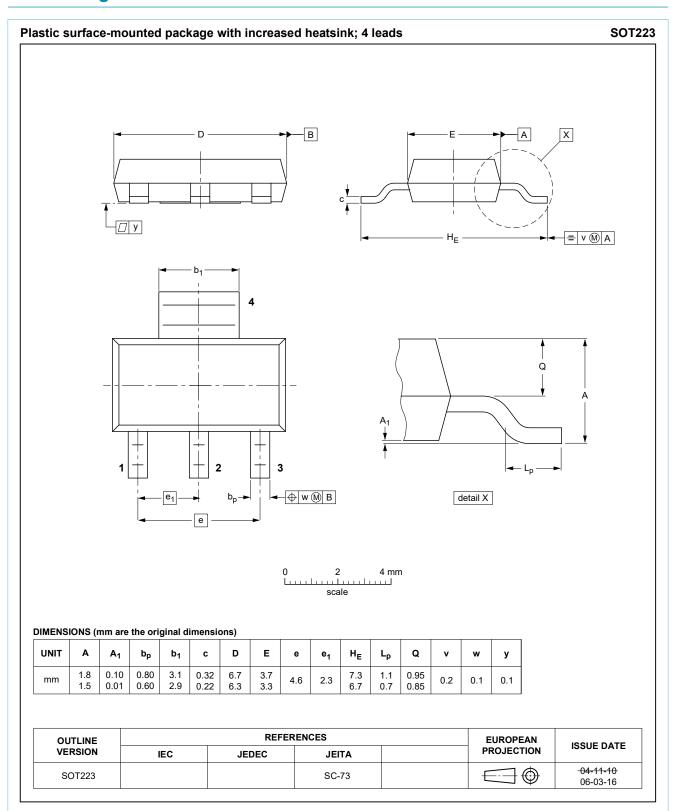
 V_o = 1.27 V; R_s = 0.091 Ω

(1) $T_j = 125$ °C; typical values (2) $T_j = 125$ °C; maximum values (3) $T_j = 25$ °C; maximum values

Fig. 12. On-state current as a function of on-state voltage



10. Package outline



11. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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For more information, please visit: http://www.ween-semi.com
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